



FMMT416

NPN HIGH VOLTAGE AVALANCHE TRANSISTOR IN SOT23

Features

- 60A Peak Avalanche Current
- BV_{CBO} > 315V
- BVcFo > 100V
- Specifically Designed for Avalanche Mode Operation
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads.
 Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.008 grams (Approximate)

Description

The FMMT416 is a silicon planar bipolar transistor designed for operating in avalanche mode. Tight process control and low inductance packaging combine to produce high-current pulses with fast edges.

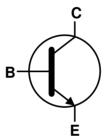
Applications

- Laser Diode Drivers for Ranging and Measurement (LIDAR)
- Radar Systems
- Fast Edge Switch Generator
- High-Speed Pulse Generators

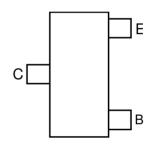








Device Symbol



Top View Pin-Out

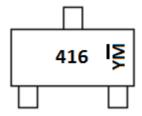
Ordering Information (Note 4)

| Part Number | Marking | Reel Size (inches) | Tape Width (mm) | Quantity Per Reel |
|-------------|---------|--------------------|-----------------|-------------------|
| FMMT416TD | 416 | 7 | 8 | 500 |
| FMMT416TA | 416 | 7 | 8 | 3000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



416 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

| Year | 2019 | 2020 | 2021 | 2022 | 202 | 3 20 | 24 2 | 025 | 2026 | 2027 | 2028 | 2029 |
|-------|------|------|------|------|-----|------|------|-----|------|------|------|------|
| Code | G | Н | I | J | K | l | L | M | N | 0 | Р | Q |
| | | | | | | | | | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |



Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|---|------------------|-------|------|
| Collector-Base Voltage | V_{CBO} | 315 | V |
| Collector-Emitter Voltage | V _{CEO} | 100 | V |
| Emitter-Base Voltage | V _{EBO} | 7 | V |
| Continuous Collector Current | Ic | 500 | mA |
| Peak Collector Current (Pulse Width = 20ns) | I _{CM} | 60 | А |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit |
|---|----------|-----------------------------------|-------------|------|
| Power Dissipation | (Note 5) | P _D | 500 | mW |
| Thermal Resistance, Junction to Ambient | (Note 5) | R _{0JA} | 250 | °C/W |
| Thermal Resistance, Junction to Leads | (Note 6) | R _{0JL} | 197 | °C/W |
| Operating and Storage Temperature Range | | T _J , T _{STG} | -55 to +150 | °C |

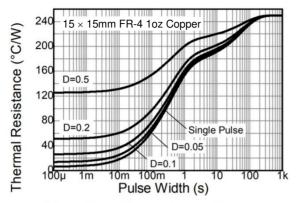
ESD Ratings (Note 7)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 400 | V | С |

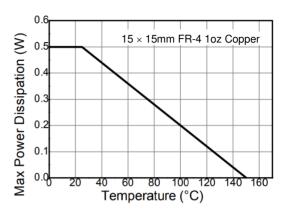
^{5.} For a device mounted with the collector lead on 15mm × 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Thermal resistance from junction to solder-point (at the end of the collector lead).
7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



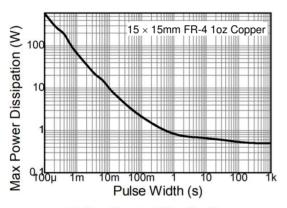
Thermal Characteristics and Derating information



Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|--|----------------------|-----|----------|-----------|----------|---|
| Collector-Base Breakdown Voltage | BV _{CBO} | 315 | _ | _ | V | $I_C = 100\mu A$ |
| Collector-Emitter Breakdown Voltage | BV _{CEO} | 100 | 1 | ı | V | $I_C = 100\mu A$ |
| Emitter-Base Breakdown Voltage | BV _{EBO} | 7 | 1 | 1 | V | $I_E = 100 \mu A$ |
| Collector Cutoff Current | I _{CBO} | | 1 | 100 10 | nA μA | V _{CB} = 310V V _{CB} = 310V, T _J = +100°C |
| Emitter Cutoff Current | I _{EBO} | | _ | 20 | nA | V _{EB} = 6V |
| Static Forward Current Transfer Ratio (Note 8) | h _{FE} | 100 | - | - | _ | $I_C = 10mA, V_{CE} = 10V$ |
| Collector-Emitter Saturation Voltage (Note 8) | V _{CE(sat)} | _ | _ | 100 | mV | $I_C = 10mA$, $I_B = 1mA$ |
| Base-Emitter Saturation Voltage (Note 8) | V _{BE(sat)} | 1 | - | 800 | mV | $I_C = 10mA$, $I_B = 1mA$ |
| Current in Second Breakdown (Pulsed) | l _{USB} | | 25 35 | | A A | $V_C = 200V, C_{CE} = 620pF$ $V_C = 250V, C_{CE} = 620pF$ |
| Collector-Emitter Inductance | L _{ce} | _ | 2.5 | _ | nΗ | Standard SOT23 leads |
| Output Capacitance | C _{cbo} | | | 8 | pF | V _{CB} = 20V, I _E = 0 f = 100MHz |
| Transition Frequency | f⊤ | 40 | _ | _ | MHz | V _{CE} = 20V, I _C = 10mA, f = 20MHz |

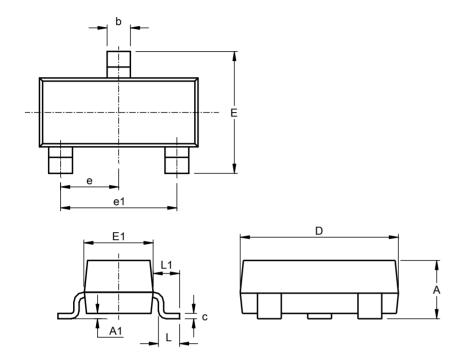
Note: 8. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)

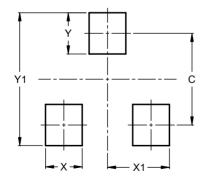


| SOT23 Type DN | | | | | | |
|---------------|----------------------|------|------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.89 | 1.12 | 1.00 | | | |
| A1 | 0.01 | 0.10 | 0.05 | | | |
| b | 0.30 | 0.51 | 0.45 | | | |
| С | 0.08 | 0.20 | 0.10 | | | |
| D | 2.80 | 3.04 | 3.00 | | | |
| Е | 2.10 | 2.64 | 2.42 | | | |
| E1 | 1.20 | 1.40 | 1.37 | | | |
| е | 0.95 REF | | | | | |
| e1 | 1.90 REF | | | | | |
| L | 0.25 | 0.60 | 0.30 | | | |
| L1 | 0.45 | 0.62 | 0.54 | | | |
| All | All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23 (Type DN)



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 2.0 |
| Х | 0.8 |
| X1 | 1.35 |
| Υ | 0.9 |
| Y1 | 2.9 |



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